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NXP Semiconductors/Freescale Semiconductor, Inc. PMEG2002AESF,315

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Datasheet of PMEG2002AESF,315 - DIODE SCHOTTKY 20V 200MA 2DSN Contact us: sales@integrated-circuit.com Website: www.integrated-circuit.com



Product data sheet

1. General description

Planar Maximum Efficiency General Application (MEGA) Schottky barrier rectifier with an integrated guard ring for stress protection in a DSN0603-2 (SOD962-2) leadless ultra small Surface-Mounted Device (SMD) package.

2. Features and benefits

- Average forward current I_{F(AV)} ≤ 0.2 A
- Reverse voltage V_R ≤ 20 V
- Low forward voltage typ. V_F = 245 mV
- Low reverse current typ. I_R = 5 μA
- · Ultra small and leadless SMD package
- Package height typ. 0.3 mm

3. Applications

- Low voltage rectification
- High efficiency DC-to-DC conversion
- Switch mode power supply
- Low power consumption applications
- Ultra high-speed switching
- LED backlight for mobile application

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
I _{F(AV)}	average forward current	δ = 0.5 ; f = 20 kHz; T_{amb} = 115 °C; square wave	[1]	-	-	0.2	А
		δ = 0.5 ; f = 20 kHz; T_{sp} = 125 °C; square wave		-	-	0.2	А
V _R	reverse voltage	T _j = 25 °C		-	-	20	V
V _F	forward voltage	I_F = 10 mA; pulsed; $t_p \le 300$ μs; $δ \le 0.02$; T_j = 25 °C		-	245	310	mV
I _R	reverse current	V _R = 10 V; T _j = 25 °C		-	5	-	μA

[1] Device mounted on a ceramic Printed-Circuit Board (PCB), Al₂O₃, standard footprint.





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5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	K	cathode[1]		1 - 1 - 2
2	А	anode		sym001
			Transparent top view	
			DSN0603-2 (SOD962-2)	

^[1] The marking bar indicates the cathode.

6. Ordering information

Table 3. Ordering information

Type number	Package	ackage				
	Name	Description	Version			
PMEG2002AESF	DSN0603-2	Leadless ultra small package; 2 terminals; body $0.6 \times 0.3 \times 0.3$ mm	SOD962-2			

7. Marking

Table 4. Marking codes

Type number	Marking code
PMEG2002AESF	A

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V_R	reverse voltage	T _j = 25 °C		-	20	V
I _F	forward current	T _{sp} ≤ 120 °C		-	0.28	Α
I _{F(AV)}	average forward current	δ = 0.5 ; f = 20 kHz; T_{amb} = 115 °C; square wave	[1]	-	0.2	А
		δ = 0.5 ; f = 20 kHz; T _{sp} = 125 °C; square wave		-	0.2	А
I _{FRM}	repetitive peak forward current	$t_p \le 1 \text{ ms}; \ \delta \le 0.25$		-	2	Α
I _{FSM}	non-repetitive peak forward current	t_p = 8 ms; $T_{j(init)}$ = 25 °C; square wave		-	4.5	Α
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C	<u>[2]</u>	-	325	mW

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Symbol	Parameter	Conditions		Min	Max	Unit
			[3]	-	525	mW
			[1]	-	950	mW
Tj	junction temperature			-	125	°C
T _{amb}	ambient temperature			-55	125	°C
T _{stg}	storage temperature			-65	150	°C

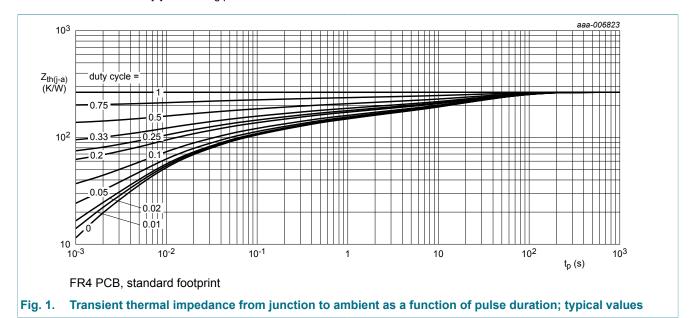
- [1] Device mounted on a ceramic Printed-Circuit Board (PCB), Al₂O₃, standard footprint.
- Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for anode and cathode 1 cm² each.

Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
R _{th(j-a)} thermal resistance from junction to ambient		in free air	[1][2]	-	-	310	K/W
		[1][3]	-	-	190	K/W	
	ambient		[1][4]	-	-	105	K/W
R _{th(j-sp)}	thermal resistance from junction to solder point		[5]	-	-	40	K/W

- [1] For Schottky barrier diodes thermal runaway has to be considered, as in some applications the reverse power losses P_R are a significant part of the total power losses.
- Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for anode and cathode 1 cm² each.
- Device mounted on a ceramic PCB, Al₂O₃, standard footprint.
- Soldering point of cathode tab.



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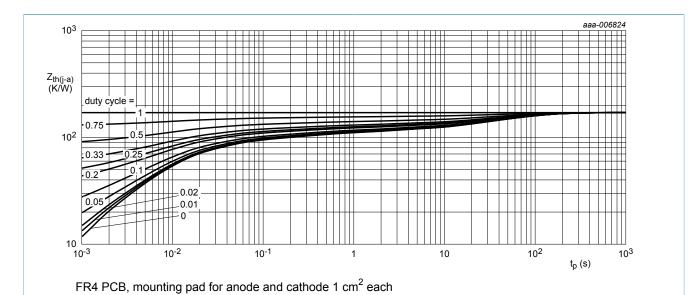
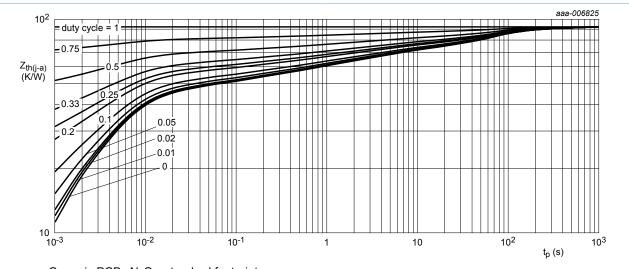


Fig. 2. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values



Ceramic PCB, Al₂O₃, standard footprint

Fig. 3. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

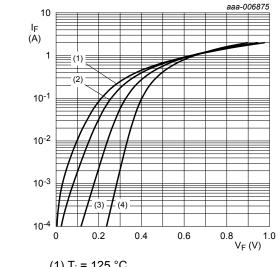
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10. Characteristics

Table 7. **Characteristics**

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _F forward voltage	forward voltage	I_F = 0.1 mA; pulsed; t_p ≤ 300 μs; δ ≤ 0.02 ; T_j = 25 °C	-	120	180	mV
		I_F = 1 mA; pulsed; $t_p \le 300$ μs; $δ \le 0.02$; T_j = 25 °C	-	180	250	mV
		I_F = 10 mA; pulsed; $t_p \le 300 \text{ μs}$; $\delta \le 0.02$; T_j = 25 °C	-	245	310	mV
		I_F = 100 mA; pulsed; $t_p \le 300$ μs; $δ \le 0.02$; T_j = 25 °C	-	330	380	mV
		I_F = 200 mA; pulsed; $t_p \le 300$ μs; $δ \le 0.02$; T_j = 25 °C	-	375	420	mV
I _R reve	reverse current	V _R = 6 V; T _j = 25 °C	-	3.2	20	μA
		V _R = 10 V; T _j = 25 °C	-	5	-	μA
		V _R = 20 V; T _j = 25 °C	-	10	45	μA
C _d	diode capacitance	V _R = 1 V; f = 1 MHz; T _j = 25 °C	-	25	-	pF
		V _R = 10 V; f = 1 MHz; T _j = 25 °C	-	10	-	pF
t _{rr}	reverse recovery time	I_F = 200 mA; I_R = 200 mA; $I_{R(meas)}$ = 40 mA; T_j = 25 °C	-	1.9	-	ns



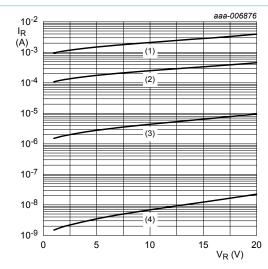


(2)
$$T_i = 85 \, ^{\circ}C$$

(3)
$$T_j = 25$$
 °C

(4)
$$T_j = -40 \, ^{\circ}\text{C}$$

Forward current as a function of forward Fig. 4. voltage; typical values



(1) $T_j = 125 \, ^{\circ}\text{C}$

(2)
$$T_i = 85 \,^{\circ}C$$

(3)
$$T_i = 25 \,^{\circ}C$$

(4)
$$T_i = -40 \, ^{\circ}C$$

Fig. 5. Reverse current as a function of reverse voltage; typical values

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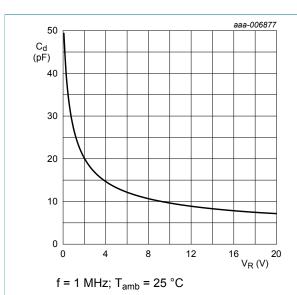
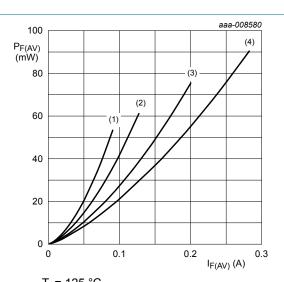


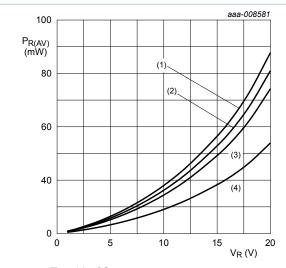
Fig. 6. Diode capacitance as a function of reverse voltage; typical values



 $T_j = 125 \text{ °C}$ (1) $\delta = 0.1$ (2) $\delta = 0.2$

(3) $\delta = 0.5$ (4) $\delta = 1$

Fig. 7. Average forward power dissipation as a function of average forward current; typical values



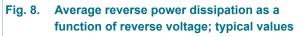
 $T_j = 125 \,^{\circ}\text{C}$

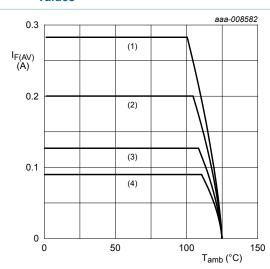
(1) δ = 1 (DC)

(2) δ = 0.9; f = 20 kHz

(3) δ = 0.8; f = 20 kHz

(4) δ = 0.5; f = 20 kHz





FR4 PCB, standard footprint

 $T_j = 125 \,^{\circ}C$

 $(1) \delta = 1$

 $(2) \delta = 0.5$

 $(3) \delta = 0.2$

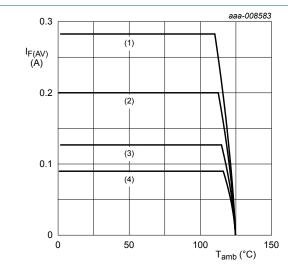
 $(4) \delta = 0.1$

Fig. 9. Average forward current as a function of ambient temperature; typical values

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FR4 PCB, mounting pad for anode and cathode 1

cm² each

T_i = 125 °C

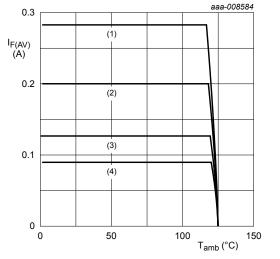
 $(1) \delta = 1$

 $(2) \delta = 0.5$

 $(3) \delta = 0.2$

 $(4) \delta = 0.1$

Fig. 10. Average forward current as a function of ambient temperature; typical values



Ceramic PCB, Al₂O₃, standard footprint

 $T_j = 125 \, ^{\circ}C$

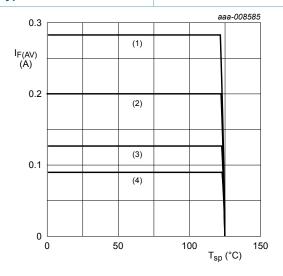
 $(1) \delta = 1$

(2) $\delta = 0.5$

(3) $\delta = 0.2$

 $(4) \delta = 0.1$

Fig. 11. Average forward current as a function of ambient temperature; typical values



T_i = 125 °C

 $(1) \delta = 1$

 $(2) \delta = 0.5$

 $(3) \delta = 0.2$

 $(4) \delta = 0.1$

Fig. 12. Average forward current as a function of solder point temperature; typical values

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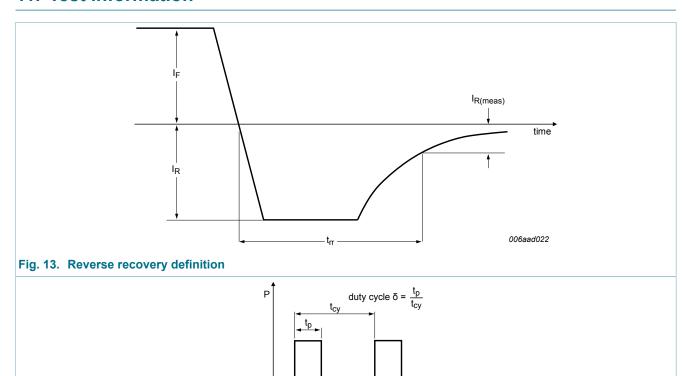


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11. Test information

Fig. 14. Duty cycle definition



The current ratings for the typical waveforms are calculated according to the equations: $I_{F(AV)} = I_M \times \delta$ with I_M defined as peak current, $I_{RMS} = I_{F(AV)}$ at DC, and $I_{RMS} = I_M \times \sqrt{\delta}$ with I_{RMS} defined as RMS current.

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12. Package outline

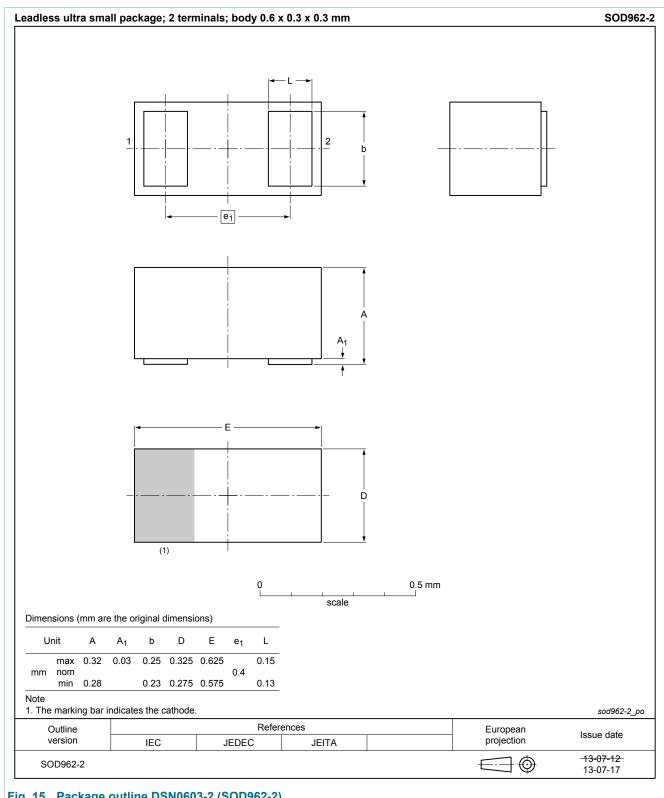


Fig. 15. Package outline DSN0603-2 (SOD962-2)

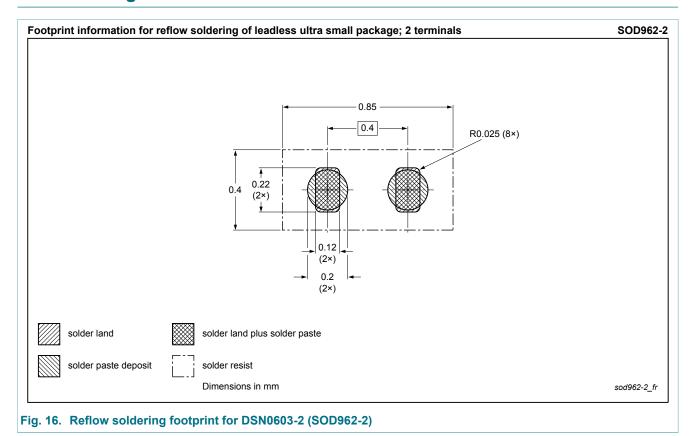
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13. Soldering



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14. Revision history

Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes				
PMEG2002AESF v.3	20140122	Product data sheet	-	PMEG2002AESF v.2				
Modifications:	 Features and benef 	Features and benefits: corrected						
PMEG2002AESF v.2	20131008	Product data sheet	-	PMEG2002AESF v.1				
PMEG2002AESF v.1	20130301	Objective data sheet	-	-				

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15. Legal information

15.1 Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
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20 V, 0.2 A low VF MEGA Schottky barrier rectifier

16. Contents

1	General description	1
2	Features and benefits	1
3	Applications	1
4	Quick reference data	1
5	Pinning information	2
6	Ordering information	2
7	Marking	2
8	Limiting values	2
9	Thermal characteristics	3
10	Characteristics	5
11	Test information	8
12	Package outline	9
13	Soldering	10
14	Revision history	11
15	Legal information	12
15.1	Data sheet status	12
15.2	Definitions	12
15.3	Disclaimers	12
15.4	Trademarks	13

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